IrMn cap layer を用いた GdFe 垂直磁化膜でのスピンオービットトルク 磁化反転の観察

Observation of spin-orbit torque magnetization switching in Gd-Fe perpendicular magnetized wire with IrMn cap layer

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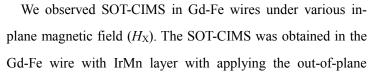
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[Introduction] Magnetization switching using spin orbit torque (SOT) has attracted significant attention because it can be applied for Magnetic Random Access Memory (MRAM). The SOT is considered to have the higher potential for manipulating magnetization than conventional spin-transfer torque (STT) for two reasons. One is the small power consumption due to the faster magnetization switching than that using STT. The other reason is the small bit error rate owing to three terminals of SOT, which enable to separate the writing and reading paths. However, it is necessary to decrease the critical current density (J_C) for CIMS to realize a memory device using the SOT. Recently, a large spin Hall effect in IrMn have been reported although it is typical antiferromagnetic material, because it has a Ir. In this study, we investigate CIMS in Gd-Fe wire with the IrMn layer to decrease the J_C .

[Experiment] The Ta/Gd-Fe/IrMn and the Ta/Gd-Fe multilayer films were deposited on a thermally oxidized Si substrates by using DC magnetron sputtering. The 5-µm-wide Hall bars were fabricated by electron beam lithography. The SOT-CIMS was observed by using anomalous Hall effect in the in-plane magnetic field.

[Result] We observed the shifted Hall loop in Gd-Fe wire with IrMn layer although it has perpendicular anisotropy. It means that the magnetization in Gd-Fe layer was pinned perpendicularly by the IrMn layer.



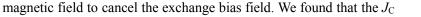


Fig. 1 Hx dependence of J_C

in the Gd-Fe wire with IrMn layer was smaller than that without IrMn layer as shown in Figure 1.

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